L Number	Hits	Search Text	DB	Time stamp
10	1238	118/52.ccls.	USPAT;	2004/07/14 13:09
			US-PGPUB;	
			EPO; JPO;	
	i '		DERWENT;	
	!	l	IBM_TDB	
11	1379	118/52,501.ccls.	USPAT;	2004/07/14 13:18
			US-PGPUB;	
			EPO; JPO; DERWENT:	
			IBM_TDB	
12	916	118/52,501.ccls. and (rotary or rotat\$3)	USPAT;	2004/07/14 13:29
'-	, 0,0	(10tally 51 15tall)	US-PGPUB:	2004/07/14 10:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	469	(118/52,501.ccls. and (rotary or rotat\$3)) and vertical\$2	USPAT;	2004/07/14 13:29
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
14	385	((118/52,501.ccls. and (rotary or rotat\$3)) and vertical\$2) and	IBM_TDB USPAT;	2004/07/14 13:25
'	303	((110/32,301.ccis. and (lotary of fotal \$3)) and vertical \$2) and (semiconductor or wafer or substrate)	US-PGPUB;	2004/01/14 13.25
		(EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	48	(((118/52,501.ccls. and (rotary or rotat\$3)) and vertical\$2) and	USPAT;	2004/07/14 13:30
		(semiconductor or wafer or substrate)) and ((collect\$3 or	US-PGPUB;	
		recover\$3) near2 (waste or liquid or fluid))	EPO; JPO;	
			DERWENT;	
16	2129	118/52,320,321,501.ccls.	IBM_TDB USPAT;	2004/07/14 13:19
	2123	110/02,020,021,001.0013.	US-PGPUB;	2004/07/14 13.19
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
17	47	118/52,320,321,501.ccls. and (trough)	USPAT;	2004/07/14 13:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
20	1284	118/52,320,321,501.ccls. and (rotary or rotat\$3)	USPAT;	2004/07/14 13:25
	1204	110/02,020,021,001.00.0. und (10.01) of 10.01(0)	US-PGPUB;	2004/07/14 15.25
			EPO; JPO;	
	,		DERWENT;	
		, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	IBM_TDB	
21	685	(118/52,320,321,501.ccls. and (rotary or rotat\$3)) and	USPAT;	2004/07/14 13:25
[1	vertical\$2	US-PGPUB;	
			EPO; JPO; DERWENT;	
	,		IBM_TDB	
22	457	((118/52,320,321,501.ccls. and (rotary or rotat\$3)) and	USPAT;	2004/07/14 13:25
		vertical\$2) and (semiconductor or wafer or substrate)	US-PGPUB;	
	,	,	EPO; JPO;	
	,	·	DERWENT;	
		(((440)50,000,004,504,551,551,551,551,551,551,551,551,551,55	IBM_TDB	
23	51	(((118/52,320,321,501.ccls. and (rotary or rotat\$3)) and	USPAT;	2004/07/14 13:27
		vertical\$2) and (semiconductor or wafer or substrate)) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))	US-PGPUB;	
	İ	((conscies of recoveres) fleatz (waste of figure of fluid))	EPO; JPO; DERWENT;	
			IBM_TDB	
24	754	156/345.11,345.18,345.19,345.51,345.55.ccls.	USPAT:	2004/07/14 13:29
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	T			
25	18	156/345.11,345.18,345.19,345.51,345.55.ccls. and trough	USPAT; US-PGPUB;	2004/07/14 13:29
			EPO; JPO;	
			DERWENT; IBM_TDB	
26	300	156/345.11,345.18,345.19,345.51,345.55.ccls. and (rotary or	USPAT;	2004/07/14 13:29
		rotat\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
27	189	(156/345.11,345.18,345.19,345.51,345.55.ccls. and (rotary or	IBM_TDB USPAT:	2004/07/14 13:30
		rotat\$3)) and vertical\$2	US-PGPUB;	2004/01/11/10:00
			EPO; JPO;	
			DERWENT;	
28	18	((156/345.11,345.18,345.19,345.51,345.55.ccls. and (rotary or	IBM_TDB USPAT;	2004/07/14 13:30
20		rotat\$3)) and vertical\$2) and ((collect\$3 or recover\$3) near2	US-PGPUB;	2004/07/14 13:30
		(waste or liquid or fluid))	EPO; JPO;	
			DERWENT;	
	_	(hidawki maan) mawaaka) in	IBM_TDB	0004/07/40 44 40
-	5	(hideyuki near2 murooka).in.	USPAT; US-PGPUB;	2004/07/12 11:42
			EPO; JPO;	•
			DERWENT;	
			IBM_TDB	
-	41	(masato near2 tsuchiya).in.	USPAT;	2004/07/12 11:40
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	16	(shunichi near2 ogasawara).in.	USPAT;	2004/07/12 11:41
		,	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	5	(hideyuki near2 murooka).in.	USPAT;	2004/07/12 11:42
			US-PGPUB; EPO; JPO;	
			DERWENT:	
			IBM_TDB	
-	61	(Mimasu adj Semiconductor).as.	USPAT;	2004/07/12 11:44
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	3806	134/95.2,95.3,102.3,104.2,149,153,157,902.ccls.	USPAT;	2004/07/12 11:51
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	1627	134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary	USPAT;	2004/07/14 13:09
		or rotat\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	1009	(134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary	USPAT;	2004/07/14 13:09
		or rotat\$3)) and vertical\$2	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	692	((134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary	USPAT;	2004/07/14 13:10
		or rotat\$3)) and vertical\$2) and (semiconductor or wafer or	US-PGPUB;	
		substrate)	EPO; JPO;	
			DERWENT; IBM_TDB	
			.5100	L

-	139	(((134/95.2,95.3,102.3,104.2,149,153,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/14 13:10
-	4570	134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls.	IBM_TDB USPAT; US-PGPUB;	2004/07/12 11:51
	4042	404/05 0 05 0 400 0 404 0 400 407 440 450 455 457 000 !	EPO; JPO; DERWENT; IBM_TDB	0004/07/40 44 70
- 	1813	134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/12 11:56
-	1120	(134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/12 11:51
-	716	((134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/12 11:52
-	152	((((134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and ((collect\$3 or recover\$3) near2 (waste or liquid or fluid))		2004/07/12 11:58
-	25	134/104.2.ccls. and (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/12 12:13
_	10	134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls. and (annular adj trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/12 11:57
_	9	438/\$.ccls. and (annular adj trough)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/12 11:57
-	205	(((134/95.2,95.3,102.3,104.2,109,137,149,153,155,157,902.ccls and (rotary or rotat\$3)) and vertical\$2) and (semiconductor or wafer or substrate)) and annular		2004/07/12 11:58
-	17	134/104.2.ccls. and (annular)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/12 12:02
-	210	134/104.2.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/12 12:19
-	59	134/104.2.ccls. and (rotary or rota\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/12 12:19
			IBM_TDB	

		404(0)	LICEAT	0004/07/40 40 10
-	0	134/\$.ccls. and (semiconductor or wafer or substrate) and (waste near2 trough)	USPAT; US-PGPUB;	2004/07/12 13:46
	1	(Waste hearz dough)	EPO; JPO;	
			DERWENT:	,
	İ		IBM TDB	
	9	134/\$.ccls. and (semiconductor or wafer or substrate) and	USPAT:	2004/07/12 13:50
-		(annular near2 trough)	US-PGPUB;	2004/07/12 13:50
		(annular nearz trough)	EPO; JPO;	
			DERWENT;	
	142	(composituator or wafer or substrate) and (ensular near)	IBM_TDB	2004/07/12 12:47
-	142	(semiconductor or wafer or substrate) and (annular near2 trough)	USPAT;	2004/07/12 13:47
		(lough)	US-PGPUB;	•
			EPO; JPO; DERWENT;	
			IBM TDB	
	96	((semiconductor or wafer or substrate) and (annular near2		2004/07/42 42:40
-	30	trough)) and (rotary or rotat\$3)	USPAT; US-PGPUB;	2004/07/12 13:48
1		l trough)) and (rotary or rotates)	EPO; JPO;	
	į		DERWENT:	
			IBM TDB	
_	0	134/\$.ccls. and (semiconductor or wafer or substrate) and	USPAT;	2004/07/12 13:55
	ı	((annular near2 trough) with vertical\$2)	US-PGPUB:	2004/07/12 13:33
		ן (מוווישומו ווכמוב נוסטקוו) אונוו צפונוסמושב)	EPO; JPO;	
			DERWENT:	
			IBM TDB	
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